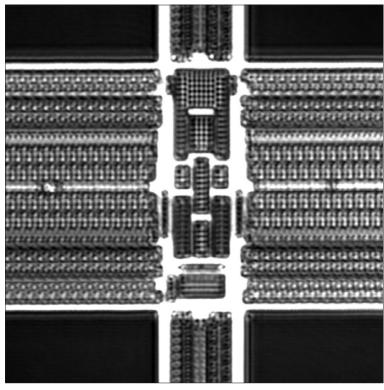
A single Super High Resolution SIL assembly that works for photoemission and laser techniques, at various sample thicknesses











Features

- Numerical aperture (N.A.): 3.1
 - Maximum resolution: approx. 120 nm
 - Sensitivity: 10 times (compared with a standard NIR100× lens)
- Available both for photoemission and laser applications (IR-OBIRCH analysis, EO probing, etc.)
- Swappable SIL cap architecture
 - Cover Si thicknesses from 50 μm to 795 μm
 - Easy mounting on lens body
 - Lens is automatically aligned on a device surface to get the best contact between the lens and Si surface to collect light signal most efficiently.

Applications

- Backside observation of advanced devices
 - Photoemission analysis
 - Time-resolved photoemission analysis
 - IR-OBIRCH analysis
 - DALS (Dynamic Analysis by Laser Stimulation) analysis
 - EO probing analysis



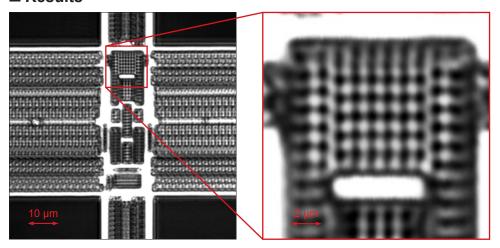
Failure Analysis Systems Option

Case study

■ Purpose Evaluation of NanoLens-SHR resolution by using an actual sample

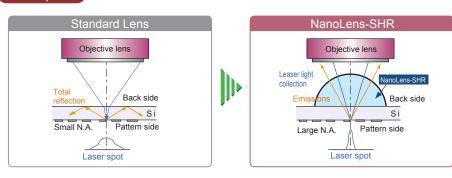
■ **Method** Taking a pattern image of a commercially available 38 nm DRAM with backside polish Light source is 1.3 µm laser.

■ Results



■ Conclusion Acquired image has no distortion. FOV 52 μm × 52 μm The 10 μm square digital zoomed image shows detailed structure clearly.

Principles



Due to the high reflection index of Si, light passing through the Si layer is not collected efficiently by an objective lens. By putting a Si lens directly on the Si surface, all light that has been reflected at the boundary between Si and the lens can be collected and focused to a high N.A. objective lens. Higher light collection efficiency improves image resolution drastically.

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